



FIG.2

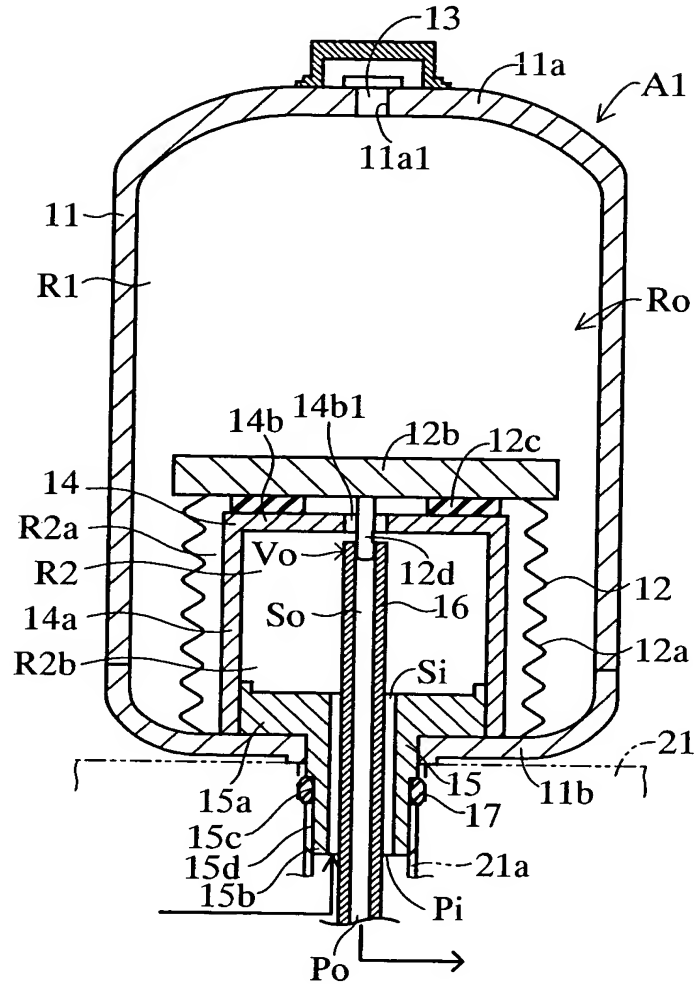


FIG.3

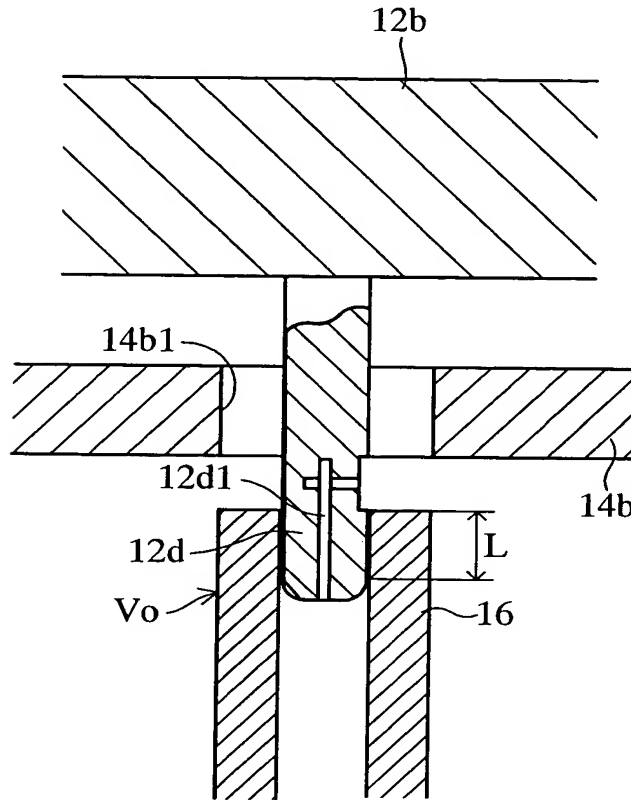


FIG.4

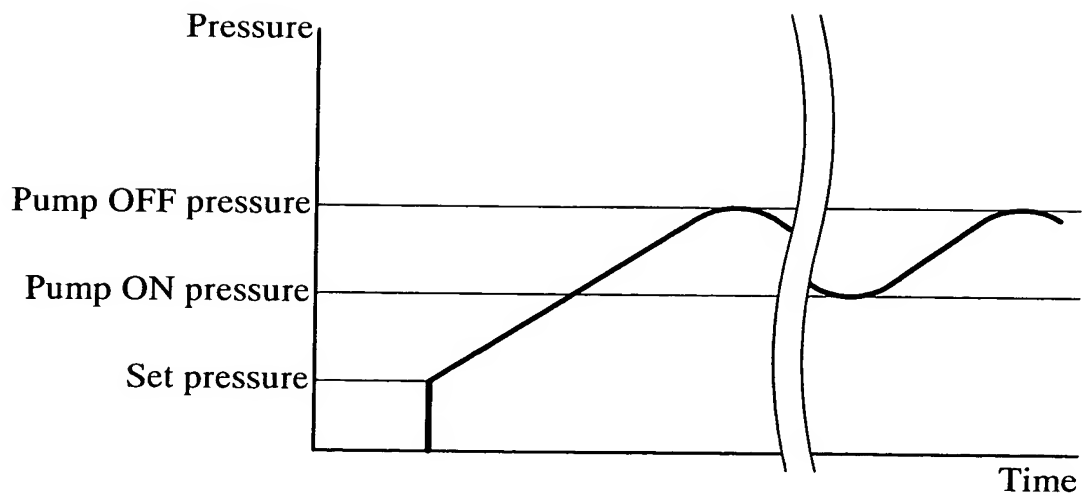
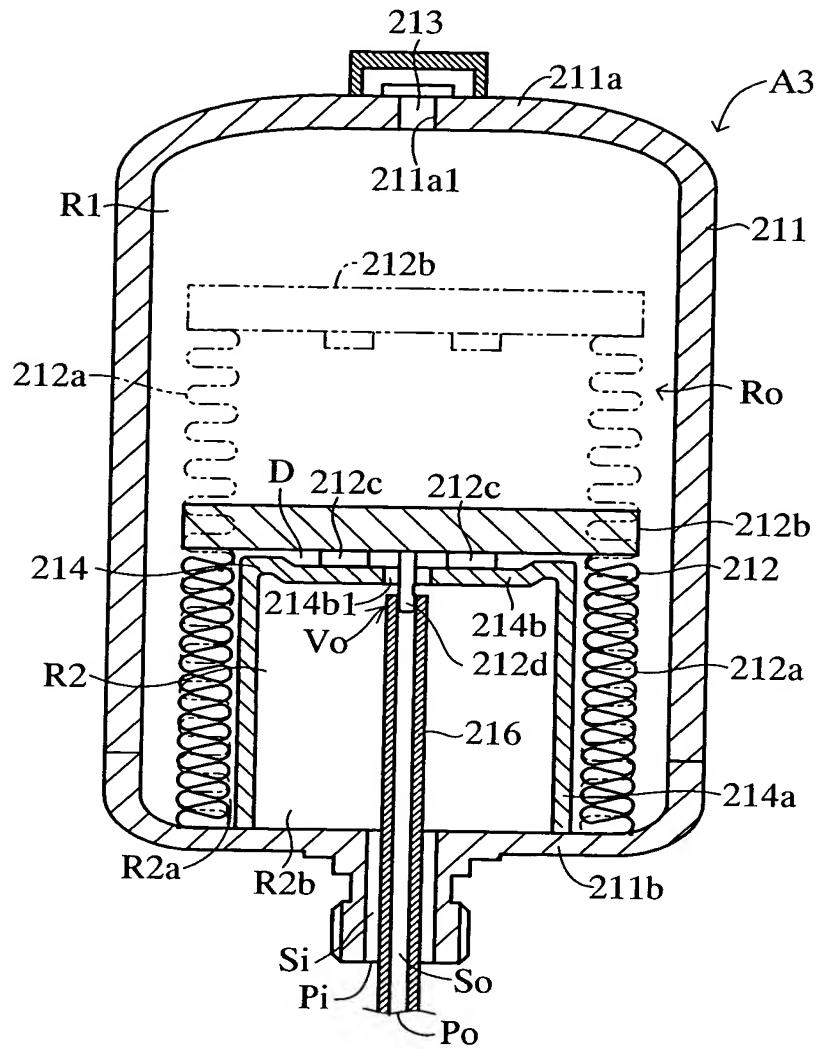




FIG.6



A detailed cross-sectional diagram of a semiconductor device. The main body consists of a substrate with a top layer labeled 311. Inside, there are several regions: R1 at the top, followed by a wavy region R2 containing sub-regions R2a and R2b. Below R2 is another wavy region 312, which contains sub-regions 312a and 312b. A central vertical channel or well is formed, containing layers labeled So and Si. Above this channel is a horizontal layer 314, which includes sub-layers 314a and 314b, and a specific point or feature 314b1. To the right of the channel, there is a region labeled Vo. At the bottom of the device, there is a base layer 315, which includes sub-layers 315a, 315c, 315d, and 315b. A contact pad or terminal 317 is shown on the right side, connected to a lead-out line Pi. Another lead-out line Po is shown at the bottom center. Various other labels like 311a, 311a1, 311b, 321, and 321a indicate different parts of the device's periphery and internal structure.

FIG.8

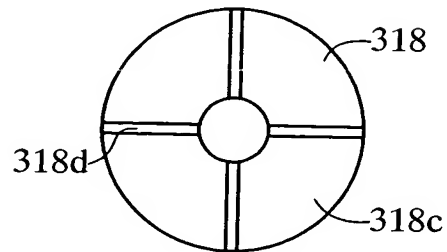


FIG.9A

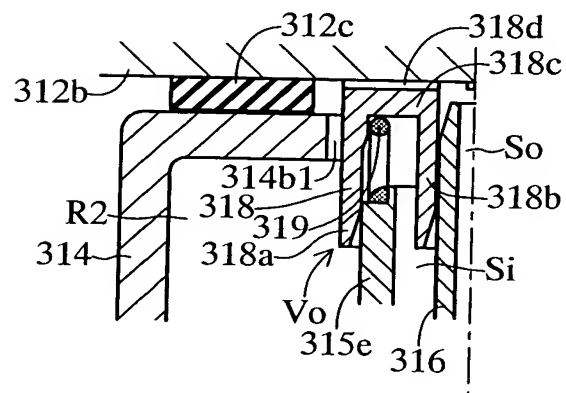


FIG.9B

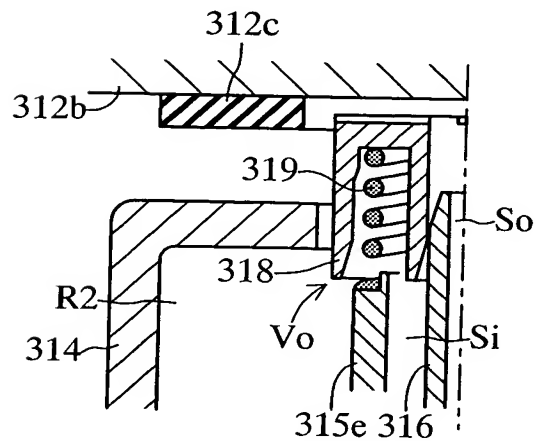






FIG.11

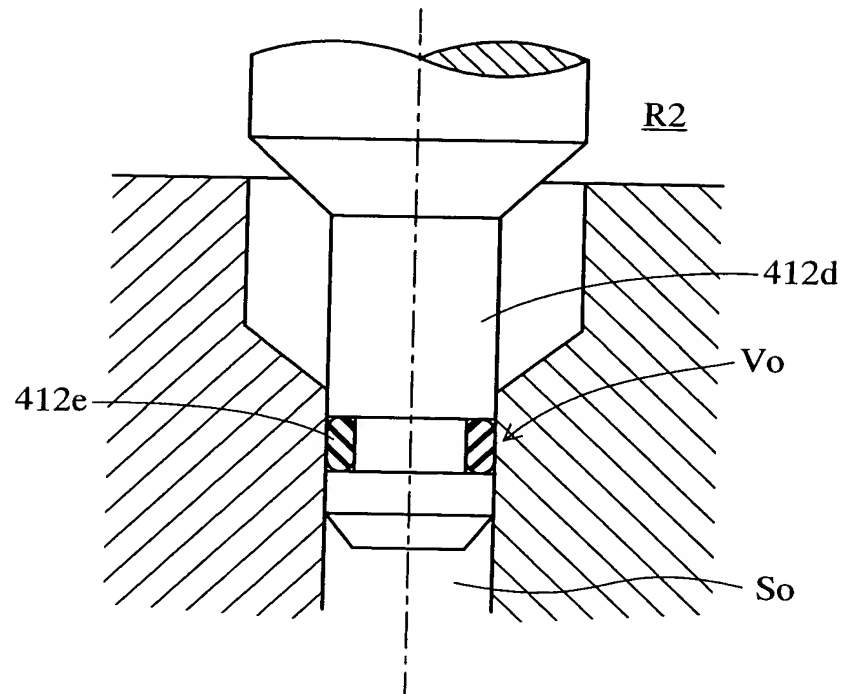


FIG.12

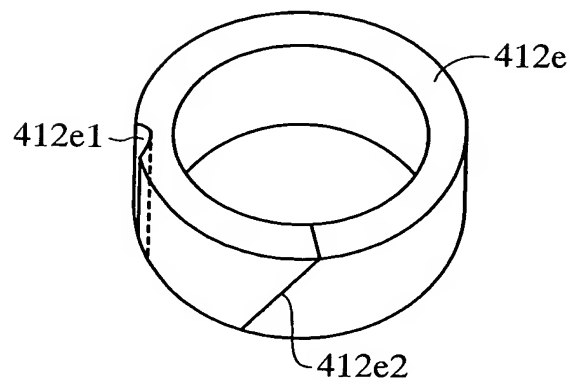


FIG.13

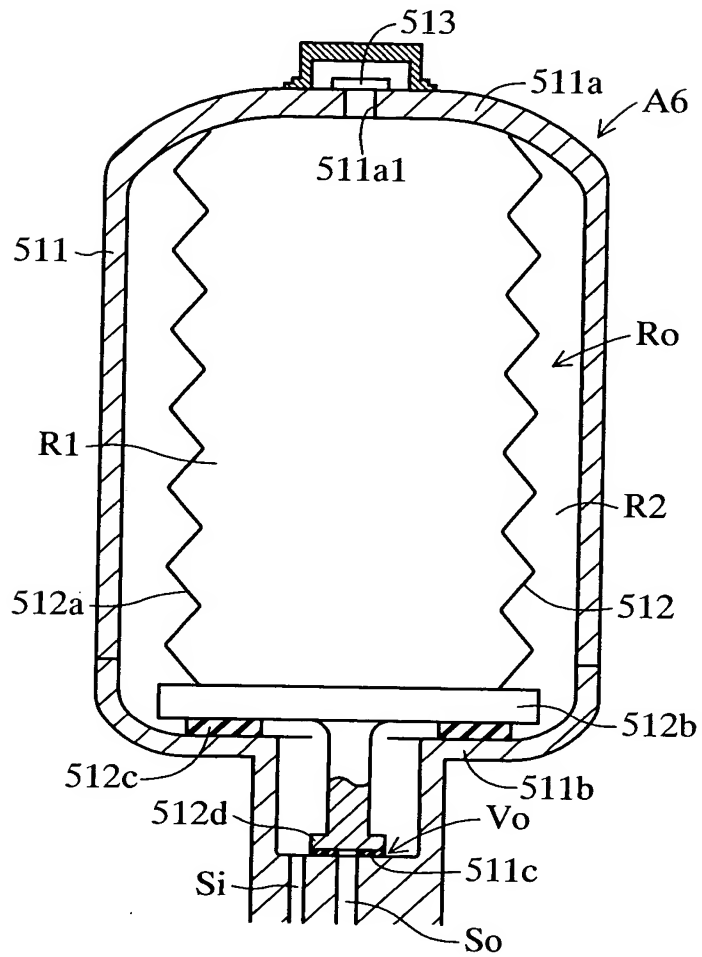


FIG.14

